

	Metal Etch
Processes	Metal etch processes
Gases/Mass flow controller Non toxic gases toxic gases	MKS 1179A for non toxic mfc, MKS1479A for toxic mfc SF6, O2,Ar,CHF3,N2 Cl2, HBr, BCl3
Electrode table temperature range	240mm heated electrode room temp to 350°C
Plasma Sources ICP power RF power for DC bias	3KW 600W
Chamber Pumping Port Pumpdown pipe Size Pumpdown pipe Heating	200mm pumping tee with 200mm branch to sealable Automatic Pressure Controller (APC) Heated
Chamber Configuration Chamber heating kit Chamber vacuum measurment Process chamber pumping config Dry pump for backing turbo Clamp process (clamp ring) Chamber Liner kit Helium cooling on electrode Base Pressure Leak rate	Heated from room temp to 80°C 100mT CM gauge, Penning gauge Alcatel ATH1300M turbo pump @ 1300l/sec Alcatel ADP122P dry mechanical pump @ 1800l/min 6" , 8" 1 set Yes < 5x 10 ⁻⁶ mtorr <2mtorr/min
Loadlock (LL) Chamber LL chamber vacuum measurment Wafer handling Dry pump for LL Base Pressure Leak rate	Pirani gauge 6" , 8" wafer Alcatel ACP15 < 9x 10 ⁻³ mtorr <3mtorr/min
Electrode table cooling Special chiller	Julaboo FP51 chiller
Software	Windows 7 and PC2000 user software
System Facitlies requirement	Provided by Cleanroom facility
Standard Warranty	12 months - parts & warranty

Al Etch rate	125nm/min
Selectivity to AZ type resist (resist profile>80°)	≥2:1
Profile angle	85°
Uniformity	
Within wafer 8"	≤±5% @7mm edge exclusion

Pt Etch rate	8nm/min
Selectivity to AZ type resist (resist profile>80°)	≥2:1
Profile angle	70°
Uniformity	
Within wafer 8"	≤±5% @7mm edge exclusion